

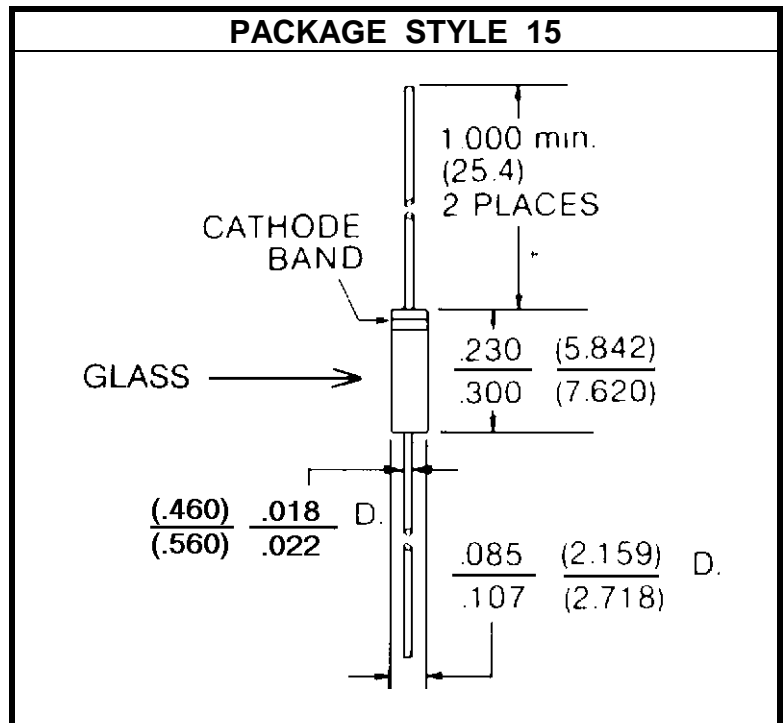
SILICON PIN DIODE

DESCRIPTION:

The **ASI 5082-3080** PIN Diode is Designed for Low Power RF Switching and Attenuating Applications.

MAXIMUM RATINGS

| | |
|-------------------------|---------------------------------|
| I | 250 mA |
| V | 100 V |
| P_{DISS} | 250 mW @ T _C = 25 °C |
| T_J | -65 °C to +150 °C |
| T_{STG} | -65 °C to +150 °C |
| T_{SOLD} | 260 °C for 5 sec. |


CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|----------------|---|---------|---------|---------|-------|
| V _R | I _R = 10 μA | 100 | | | V |
| V _F | I _F = 100 mA | | 1.0 | | V |
| τ | I _F = 50 mA I _R = 250 mA | | 1300 | | μS |
| R _S | I _F = 100 mA f = 100 MHz | | | 2.5 | Ω |
| C _t | V _R = 50 V f = 1.0 MHz | | | 0.4 | pF |
| R _H | I _F = 10 μA f = 100 MHz | 1000 | | | Ω |
| R _L | I _F = 20 mA f = 100 MHz | | | 8.0 | Ω |